

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	10.5mΩ@4.5V	27A
	14.5mΩ@2.5V	

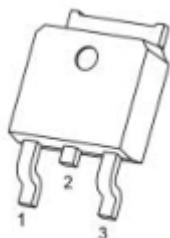
Feature

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Applications

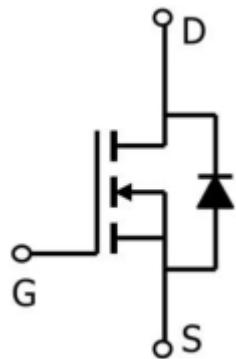
- Power switching application
- Load switching
- Uninterruptible power supply

Package



TO-252(G:1 D:2 S:3)

Circuit diagram



Marking



20N10 : Product code
** : Week code.

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	27	A
Pulsed Drain Current	I_{DM}	108	A
Maximum Power Dissipation	P_D	40	W
Thermal Resistance,Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	3.8	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Electrical characteristics

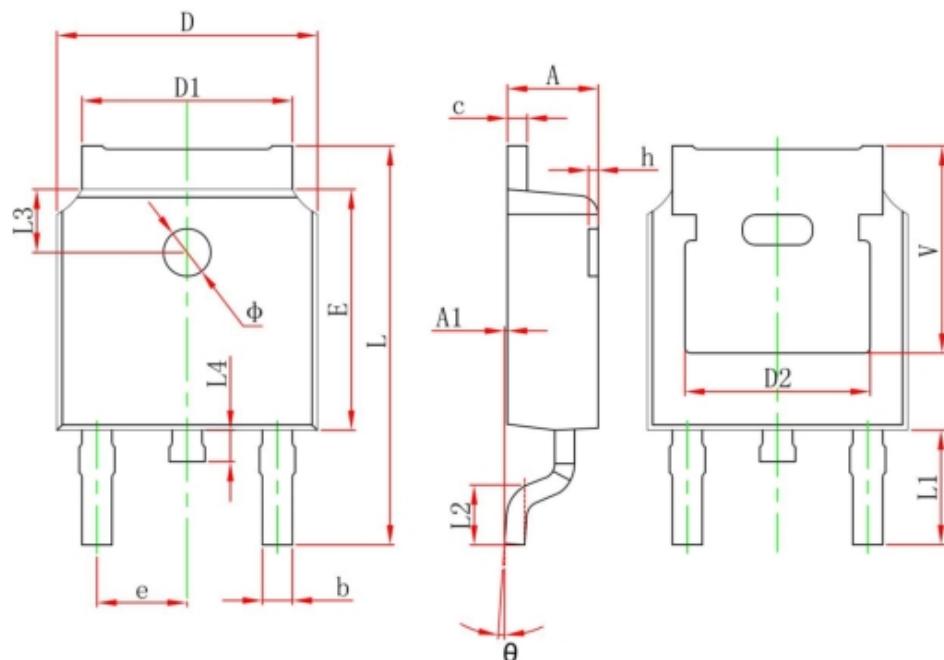
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 10\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	μA
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	0.5	0.7	1.2	V
Drain-Source On-State Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 8\text{A}$		10.5	14	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 6\text{A}$		14.5	20	
Dynamic characteristics ⁽²⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		865		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			55		
Switching Characteristics ⁽²⁾						
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DS}} = 4\text{V}, I_{\text{D}} = 4\text{A}, R_{\text{GEN}} = 5\text{V}, R_{\text{GEN}} = 1\Omega$			10	nS
Rise Time	T_{r}				20	
Turn-Off Delay Time	$T_{\text{d(off)}}$				32	
Fall Time	T_{f}				12	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽²⁾	V_{SD}	$I_{\text{S}} = 1\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V

Notes:

1. Surface Mounted on FR4 Board, $t \leq 10$ sec.
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	